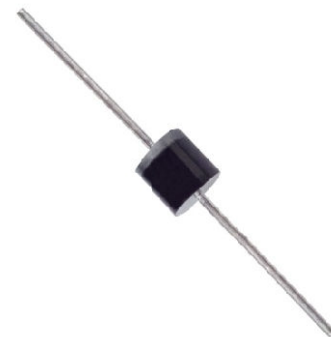


Silicon Rectifier, 10.0A

Features

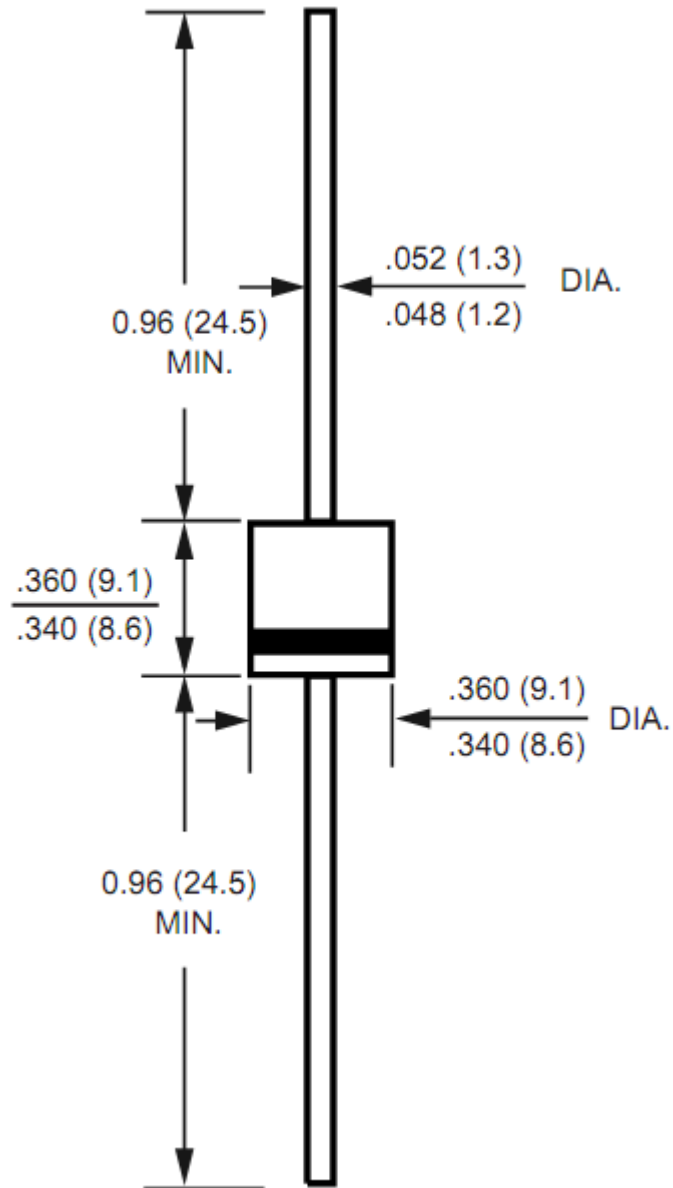
- Diffused junction
- Low cost
- Low reverse leakage current
- High current capability & low forward voltage drop
- Plastic material carrying UL recognition 94V-0
- Polarity: Color Band denotes Cathode
- Lead free finish

Thermal and Mechanical Specifications ($T_A = 25^{\circ}\text{C}$ unless otherwise specified)			
Parameters	Symbol	Values	Units
Maximum operating junction temperature range	T_J	- 55 to + 125	$^{\circ}\text{C}$
Maximum storage temperature range	T_{Stg}	- 55 to + 150	$^{\circ}\text{C}$
Typical thermal resistance junction to ambient	$R_{\theta JA}$	10	$^{\circ}\text{C}/\text{W}$
Approximate weight	W	2.1	g



JEDEC R-6

Electrical Characteristics ($T_A = 25^{\circ}\text{C}$ unless otherwise specified)										
Parameter	Symbol	10A05	10A1	10A2	10A4	10A6	10A8	10A10	Units	
Maximum repetitive peak reverse voltage	V_{RRM}	50	100	200	400	600	800	1000	V	
Maximum RMS voltage	V_{RMS}	35	70	140	280	420	560	700	V	
Maximum DC blocking voltage	V_{DC}	50	100	200	400	600	800	1000	V	
Maximum average forward output current @ $T_A = 50^{\circ}\text{C}$	$I_{F(AV)}$	10							A	
Peak forward surge current (8.3ms) single half sine-wave superimposed on rated load	I_{FSM}	600							A	
Maximum DC forward voltage drop per element @ 10 A	V_F	1.0							V	
Typical junction capacitance	CJ	150							pF	
Maximum DC reverse current at rated DC blocking voltage	$T_A = 25^{\circ}\text{C}$	I_R							10	μA
	$T_A = 100^{\circ}\text{C}$									



Dimensions in inches and (millimeters)